

Inanc Meric

List of Publications by Year in descending order

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papers

4,416
citations

687363

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21
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docs citations

21
times ranked

6982
citing authors

#	ARTICLE	IF	CITATIONS
1	Graphene Field-Effect Transistors for Radio-Frequency Flexible Electronics. IEEE Journal of the Electron Devices Society, 2015, 3, 44-48.	2.1	69
2	Properties of Self-Aligned Short-Channel Graphene Field-Effect Transistors Based on Boron-Nitride-Dielectric Encapsulation and Edge Contacts. IEEE Transactions on Electron Devices, 2015, 62, 4322-4326.	3.0	19
3	Flexible Graphene Field-Effect Transistors Encapsulated in Hexagonal Boron Nitride. ACS Nano, 2015, 9, 8953-8959.	14.6	112
4	A unified charge-current compact model for ambipolar operation in quasi-ballistic graphene transistors: Experimental verification and circuit-analysis demonstration. , 2013, , .		7
5	Chip-integrated ultrafast graphene photodetector with high responsivity. Nature Photonics, 2013, 7, 883-887.	31.4	971
6	Graphene Field-Effect Transistors with Gigahertz-Frequency Power Gain on Flexible Substrates. Nano Letters, 2013, 13, 121-125.	9.1	117
7	Graphene Field-Effect Transistors Based on Boron-Nitride Dielectrics. Proceedings of the IEEE, 2013, 101, 1609-1619.	21.3	137
8	Substrate dependent high-field transport of graphene transistors. , 2013, , .		0
9	Flexible graphene field-effect transistors for microwave electronics. , 2013, , .		2
10	Chemical Vapor Deposition-Derived Graphene with Electrical Performance of Exfoliated Graphene. Nano Letters, 2012, 12, 2751-2756.	9.1	365
11	Wafer-Scale Graphene Integrated Circuit. Science, 2011, 332, 1294-1297.	12.6	812
12	High-frequency performance of graphene field effect transistors with saturating IV-characteristics. , 2011, , .		32
13	Channel Length Scaling in Graphene Field-Effect Transistors Studied with Pulsed Current-Voltage Measurements. Nano Letters, 2011, 11, 1093-1097.	9.1	135
14	Deterministic tuning of slow-light in photonic-crystal waveguides through the C and L bands by atomic layer deposition. Applied Physics Letters, 2010, 96, .	3.3	15
15	Doping and Illumination Dependence of $1/f$ Noise in Pentacene Thin-Film Transistors. IEEE Electron Device Letters, 2010, 31, 1050-1052.	3.9	13
16	Graphene field-effect transistors based on boron nitride gate dielectrics. , 2010, , .		67
17	Semiconductor-dielectric interfacial study using spectral-spatial photocurrent probes and $1/f$ noise probe in organic field effect transistors. , 2009, , .		0
18	Controlled dielectrophoretic assembly of carbon nanotubes using real-time electrical detection. Applied Physics Letters, 2009, 94, .	3.3	20

#	ARTICLE	IF	CITATIONS
19	Graphene nanoribbon devices and quantum heterojunction devices. , 2009, , .		5
20	Current saturation in zero-bandgap, top-gated graphene field-effect transistors. Nature Nanotechnology, 2008, 3, 654-659.	31.5	1,426
21	RF performance of top-gated, zero-bandgap graphene field-effect transistors. , 2008, , .		92